

## ECE250 Lab Project #6

### Design of a Common-Emitter Audio Amplifier

April 23, 2010 (KEH)

Department of Electrical and Computer Engineering

Rose-Hulman Institute of Technology

Lab Team Members: \_\_\_\_\_

Date Performed: \_\_\_\_\_ Lab Station: \_\_\_\_\_

In this experiment you will first measure the beta of your transistor, design the amplifier circuit below (by calculating the necessary values of  $R_1$ ,  $R_2$ ,  $R_C$  and  $R_E$ ) to exhibit a specified dc Q-point, investigate Q-point stability with respect to  $\beta$  using circuit analysis, and finally predict the small-signal voltage gain and maximum symmetrical output voltage swing, and then compare your predictions against measured and simulated values.

#### ***PRELAB ASSIGNMENT:***

Since you won't know the precise value of  $\beta$  for your specific transistor ahead of time, assume  $\beta = 200$  when working through this prelab. In this prelab, please create a Maple worksheet with  $\beta$  as a variable that is defined at the top of the worksheet, so that you can simply change the value of  $\beta$  in the worksheet to recompute all the necessary values once you have measured the precise value of your BJT.

- 1) Consider the common-emitter (CE) amplifier circuit shown in Fig. L6-1. Assume that  $V_{BEON} = 0.7$  V, and that the (dual) dc power supplies are  $V_{CC} = +12$  V and  $V_{EE} = -12$  V. The desired dc bias Q-point is  **$I_{CQ} = 15$  mA and  $V_{CEQ} = 11$  V.** Note that when you Theveninize the base bias circuit, you may use Linear Superposition to find  $V_{th} = V_{OPEN\ CIRCUIT}$ . You should be able to show, using Linear Superposition, that

$$V_{th} = (+12) \frac{R_2}{R_1 + R_2} + (-12) \frac{R_1}{R_1 + R_2}$$

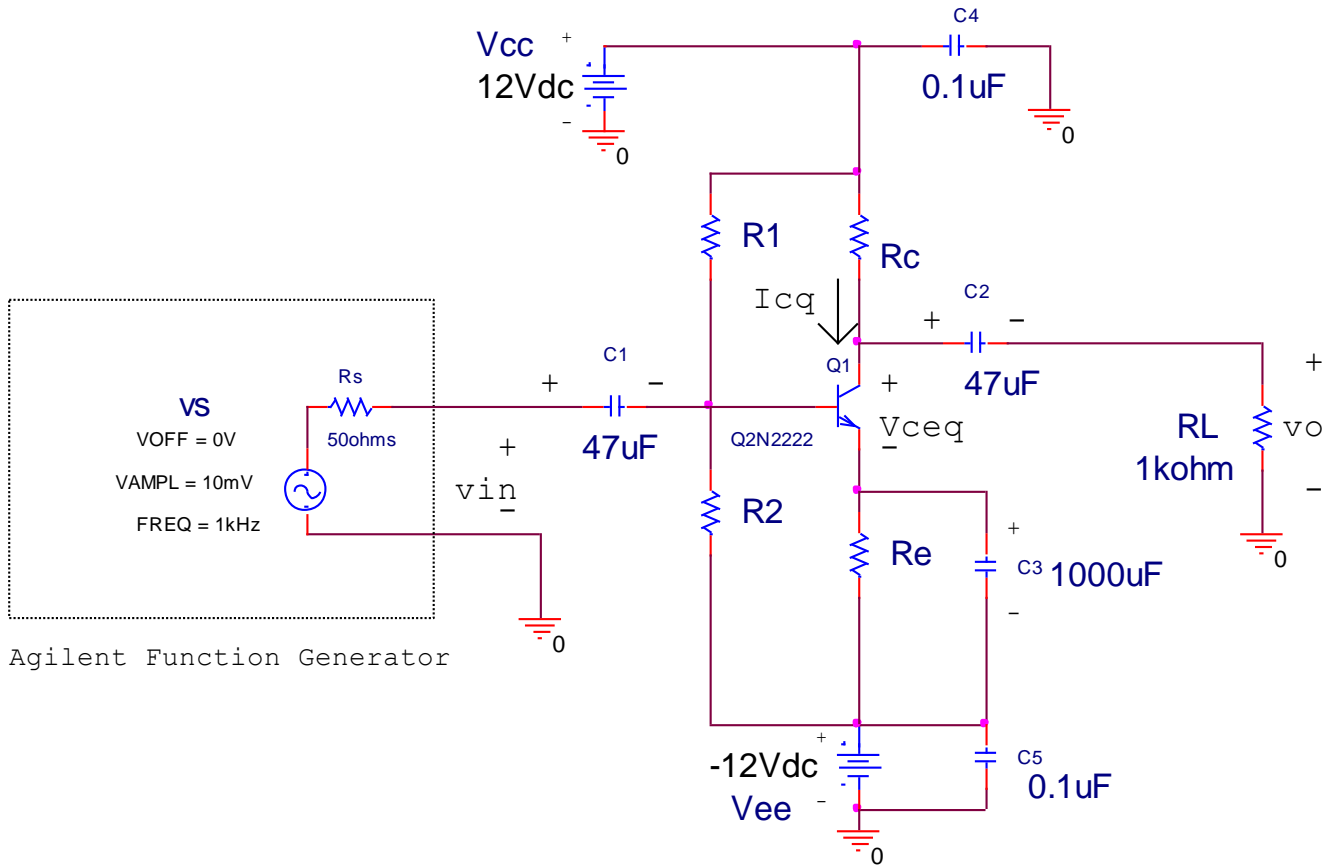
Note that the negative side of  $V_{th}$  connects to GROUND, not either  $V_{CC} = +12$  V or  $V_{EE} = -12$  V. Note that  $R_{th}$  is still  $R_1 // R_2$ , after you set the two dc power supply sources to zero.

Alternatively, we may find  $V_{th} = V_{OPEN\ CIRCUIT}$  without using Linear Superposition by writing the following node equation at the junction of the  $R_1$  and  $R_2$ , assuming that the base of the BJT has been temporarily disconnected:

$$(V_{th} - 12)/R_1 + (V_{th} - (-12))/R_2 = 0$$

Solving this equation for  $V_{th}$  should yield the same result as obtained using Linear Superposition.

**Fig. L6-1. Common Emitter (CE) NPN BJT Audio Amplifier**



- a. Design the circuit so that  $V_{RC} = 12 \text{ V}$ ,  $V_{ce} = 11 \text{ V}$ , and  $V_{RE} = 1 \text{ V}$  using the rule of thumb that  $R_{th} = 0.1(\beta_F + 1)R_E$  for good bias stability. Attach your calculations as **Exhibit A1**. (Remember units!)

Results:  $R_E = \underline{\hspace{2cm}}$   $R_C = \underline{\hspace{2cm}}$   $R_1 = \underline{\hspace{2cm}}$   $R_2 = \underline{\hspace{2cm}}$

- b. Now investigate the stability of this Q-point with respect to variation in  $\beta_F$  by recalculating the Q-point for  $\beta_F = 100$  and for  $\beta_F = 300$ , keeping the four resistors the same as in Part (a). Attach your calculations as **Exhibit A2**. (Remember units!)

Results: For  $\beta_F = 100$   $I_{CQ} = \underline{\hspace{2cm}}$   $V_{CEQ} = \underline{\hspace{2cm}}$   
 For  $\beta_F = 300$   $I_{CQ} = \underline{\hspace{2cm}}$   $V_{CEQ} = \underline{\hspace{2cm}}$

- c. Calculate below the small-signal transistor parameters:  $r_\pi$  &  $g_m$  that corresponds to the Q point when  $\beta = 200$ . Assume the 2N2222 BJT exhibits  $n = 1.3$  (since this is a discrete BJT, as opposed to an IC BJT as in our textbook where  $n = 1.0$ ), and room temperature conditions,  $V_T = 26 \text{ mV}$  (Remember units!).

Result:  $r_\pi = \underline{\hspace{2cm}}$   $g_m = \underline{\hspace{2cm}}$

- d. Draw an AC circuit model of the BJT amplifier in the space below with emitter bypass capacitor  $C_E$  in place and then a second AC model with  $C_E$  removed.

*AC Model of CE Amplifier Circuit of Fig. L6-1 with  $C_E$  in place*

*AC Model of CE Amplifier Circuit of Fig. L6-1 with  $C_E$  Removed*

- 2) With the emitter bypass capacitor in place, use the first AC model drawn above to calculate the small-signal open-circuit (unloaded) voltage gain,  $A_{V0}$ ; the small-signal input resistance,  $R_{in}$  and the small-signal output resistance,  $R_{out}$ . Also determine the (loaded) transducer voltage gain  $A_{vt} = v_o(t)/v_{in}(t)$ . Recall that  $A_{vt} = A_{V0} * R_L / (R_L + R_{out})$ . Attach your work as **Exhibit A3**.

Predicted Results:  $A_{V0} = \underline{\hspace{2cm}}$   $R_{in} = \underline{\hspace{2cm}}$   $R_{out} = \underline{\hspace{2cm}}$   $A_{vt} = \underline{\hspace{2cm}}$

- 3) Next, remove the emitter bypass capacitor. Using the second AC model drawn above, calculate the small-signal open-circuit (unloaded) voltage gain,  $A_{V0}$ ; the small-signal input resistance,  $R_{in}$  and the small-signal output resistance,  $R_{out}$ . Also determine the (loaded) transducer voltage gain  $A_{vt} = v_o(t)/v_{in}(t)$ . Recall that  $A_{vt} = A_{V0} * R_L / (R_L + R_{out})$ . Attach your work as **Exhibit A4**.

Predicted Results:  $A_{V0} = \underline{\hspace{2cm}}$   $R_{in} = \underline{\hspace{2cm}}$   $R_{out} = \underline{\hspace{2cm}}$   $A_{vt} = \underline{\hspace{2cm}}$

Perform two PSPICE transient simulations of your circuit (one with the emitter bypass capacitor  $C_E$  present, and one with  $C_E$  removed).

Use the “**Q2N2222**” transistor model found in the ORCAD 9.2 Lite Edition PSPICE’s “**EVAL**” library. Be sure to modify the  $\beta_F$  parameter that is called “**BF**” in the PSPICE model to match the  $\beta_F$  value that we are assuming in this prelab ( $BF = 200$ ). Do this by single left clicking directly on the BJT symbol until a pink dotted square selection box surrounds the entire BJT symbol. Then single right click inside this box and select “**Edit PSPICE Model**” from the menu box that appears. After changing this entry, be sure to click on **File – Save** in order to save this change you have made to the Q2N2222 device model in the PSPICE EVAL library. Later, after you have

measured your own BJT from the curve tracer, please rerun this simulation with the updated value of BF corresponding to your own transistor.

Include (1) your PSPICE schematic diagram and (2) your PSPICE transient analysis (PROBE) plot of  $v_{in}(t)$  and  $v_{o}(t)$  with maximum and minimum values of both  $v_{in}(t)$  and  $v_{o}(t)$  labeled using the “*Mark Cursor*” button icon, as discussed in our first lab. Present your simulated results for the fully bypassed case ( $C_E$  present) as **Exhibit B1**, and the unbypassed case ( $C_E$  removed) as **Exhibit B2**. Fill in the blanks below with the  $V_{CEQ}$  and  $I_{CQ}$  values (which can be read by pressing the “V” and “I” button icons) Calculate the percent deviation from the hand calculated (predicted) values for  $V_{CEQ}$ ,  $I_{CQ}$ , and also calculate the simulated  $A_{vt} = v_o(t)/v_{in}(t)$ . Compare these PSPICE simulated results for  $A_{vt}$  with the predicted value of  $A_{vt}$  obtained in Part 3 above. *The PSPICE simulated Q point and  $A_{vt}$  values should lay within 20% percent of the hand calculated values.*

	$C_E$ Present	$C_E$ Removed
<b>PSPICE RESULTS:</b> $V_{CEQ} = \underline{\hspace{2cm}}$ $I_{CQ} = \underline{\hspace{2cm}}$ $A_{vt} = \underline{\hspace{2cm}}$	$A_{vt} = \underline{\hspace{2cm}}$	$A_{vt} = \underline{\hspace{2cm}}$
<b>Hand Calculations:</b> $V_{CEQ} = 11\text{ V}$ $I_{CQ} = 15\text{ mA}$ $A_{vt} = \underline{\hspace{2cm}}$	$A_{vt} = \underline{\hspace{2cm}}$	$A_{vt} = \underline{\hspace{2cm}}$
<b>Percent Deviation:</b> $\underline{\hspace{2cm}}$ $\underline{\hspace{2cm}}$ $\underline{\hspace{2cm}}$	$\underline{\hspace{2cm}}$	$\underline{\hspace{2cm}}$

**END PRELAB**

**Prelab Answers (Parts 1 – 3)**

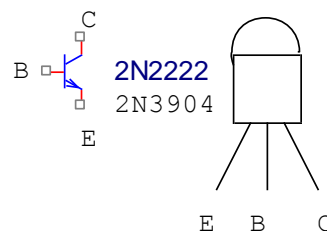
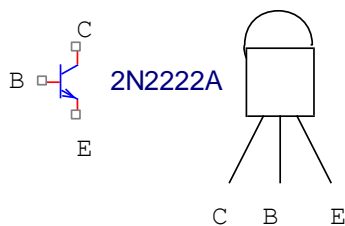
(Exhibit A1)  $R_e = 66.33\text{ ohms}$ ,  $R_c = 800\text{ ohms}$ ,  $R_1 = 17.777\text{ kohms}$ ,  $R_2 = 1.441\text{ kohms}$

(Exhibit A2) For  $\beta = 100$ , Q-point changes to  $V_{ceq} = 12.128\text{ V}$  and  $I_{cq} = 13.69\text{ mA}$   
For  $\beta = 300$ , Q-point changes to  $V_{ceq} = 10.57\text{ V}$  and  $I_{cq} = 15.49\text{ mA}$

(Exhibit A3) with  $C_E$  (emitter bypass capacitor) in place:  $A_{vo} = \text{unloaded transducer gain, with } R_L \text{ removed} = -355$   
 $r_{out} = R_c = 800\text{ ohms}$   
 $r_{in} = 336.82\text{ ohms}$   
 $A_{vt} = \text{loaded transducer gain, with } R_L \text{ in place} = -197.2$

(Exhibit A4) with  $C_E$  removed:

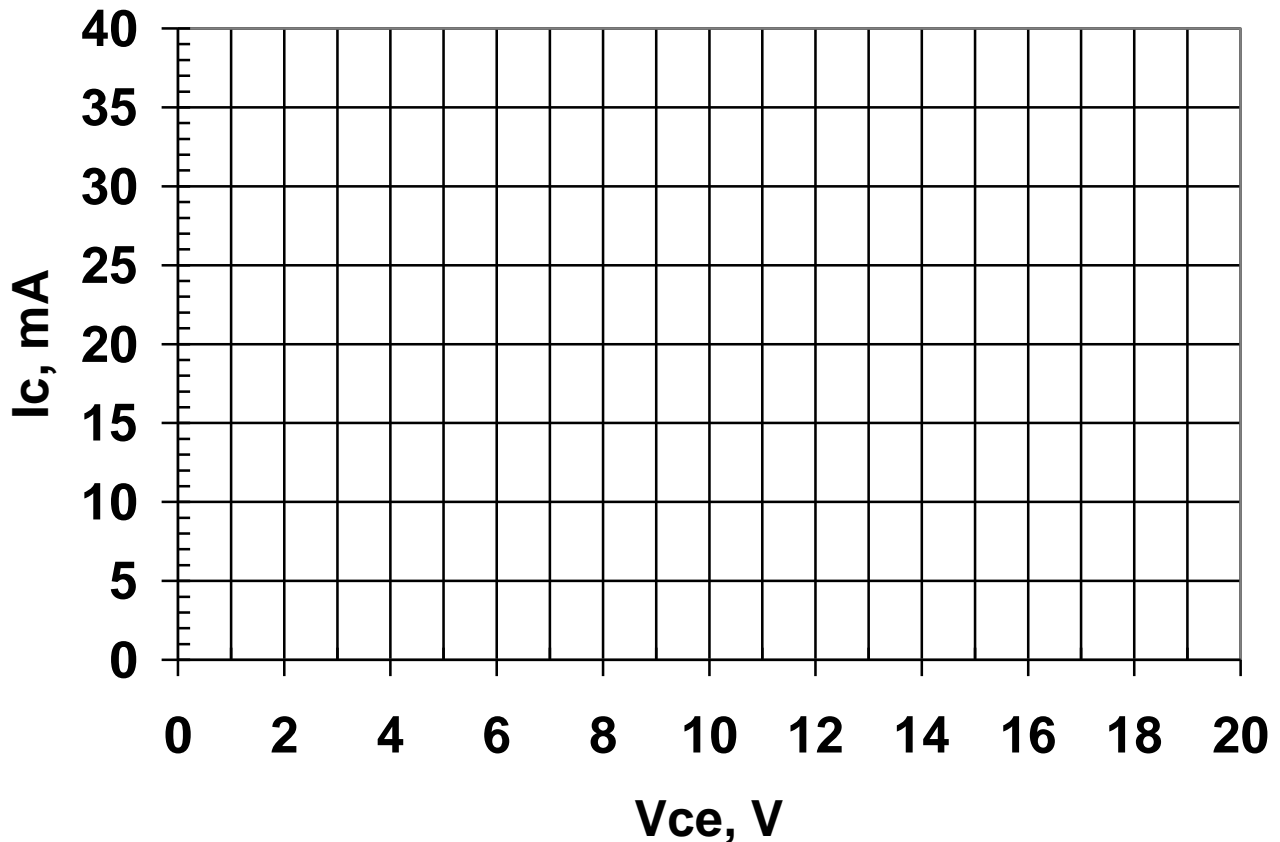
$A_{vo} = -11.61$   
 $r_{in} = 1.215\text{ kohms}$   
 $r_{out} = 800\text{ ohms}$   $A_{vt} = -6.4$



- 1) Following the instructions in the attached document in Appendix A, "Using the Sony-Tektronix 370 Curve Tracer to Trace Common-Emitter  $I_c$  vs.  $V_{ce}$  curves of an NPN BJT", display the collector characteristics ( $I_c$  vs  $V_{ce}$  for stepped values of  $I_b$ ) for a 2N2222 BJT using the curve tracer in the laboratory. (The physical pin-out of the 2N2222 is shown above.) Include a suitable sketch of these characteristics in the space below - be sure to mark the corresponding  $I_b$  value on each of the curves. From this sketch, determine an approximate value of  $\beta_F = \Delta I_c / \Delta I_b$  roughly in the vicinity of  $I_{CQ} = 15 \text{ mA}$  and  $V_{CEQ} = 11 \text{ V}$ . Select a 2N2222 BJT with a  $\beta_F$  that lies above 180, if possible.)

**Sketch of BJT CE Collector Characteristics for Your 2N2222 Transistor  
(DC and AC Load Lines to be drawn on this plot later in this lab)**

**$I_c$  vs.  $V_{ce}$  for Stepped  $I_b$  Values**



**Result:** Measured value of  $\beta_F$  at Q point ( $I_{CQ} = 15 \text{ mA}$  and  $V_{CEQ} = 11 \text{ V}$ ) = \_\_\_\_\_

Adjust the value of  $\beta_F$  in your MAPLE worksheet to match the measured result found above (Exhibit A), and attach your modified worksheet as **Exhibit C**.

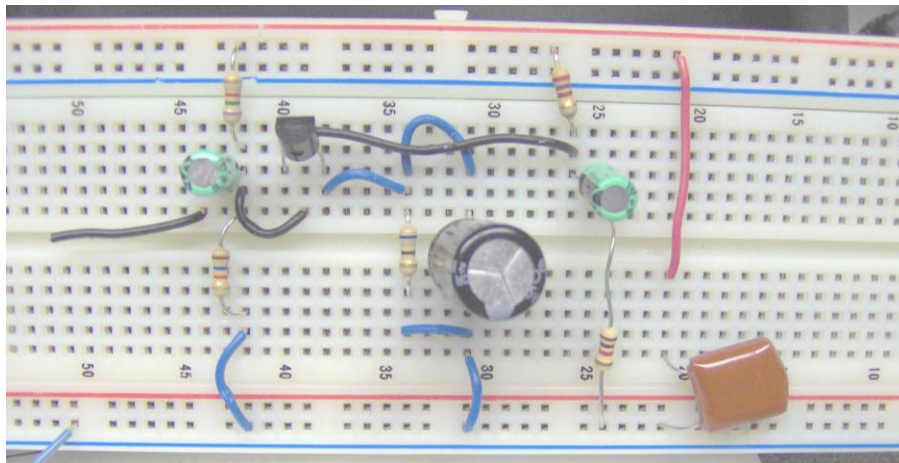
- 2) Now use the values calculated in *Exhibit C* to carefully and neatly build this circuit on your prototyping breadboard using the nearest available standard resistor values. A photograph of a similar (but not identical) breadboard appears in Fig. L6-2.

There are several breadboarding rules that I will be requiring you to follow in this course from now on, which are illustrated by Fig. L6-2:

- a. In a circuit with a single dc power supply, always use the red power distribution bus at the top of your breadboard for the Vcc dc power supply bus; likewise always use the blue power distribution bus at the bottom of your breadboard for the ground (0 V) bus. In a circuit with TWO dc power supplies (as in this lab), please use the top red bus for the Vcc = 12 V dc supply, the bottom red bus for ground (0 V), and the bottom blue bus for the Vee = -12 V dc power supply. Never use the horizontal distribution busses for any other purpose except for dc power distribution. If you pass an input or an output signal on these busses, you are increasing the chance of capacitive coupling between input and output terminals of your amplifier, and therefore promoting the chances of undesired oscillation.
- b. Always place an ac transient bypass capacitor (0.1  $\mu$ F) across the Vcc dc power bus and ground bus (and in the case of dual-dc supply circuit such as this one, across the Vee and ground bus as well). Note the capacitors C4 and C5 perform this function in Figure L6-1. These capacitors are used to absorb power supply noise caused by sudden switching transients inside the devices that are powered on the breadboard. Recall that capacitors will not pass dc, but will pass ac (noise), so the dc power is not affected by these capacitors, but any ac noise on the dc power bus will be shorted to ground by these capacitors. Sudden Vcc or Vee current demands made by one device on your breadboard can cause momentary voltage drops on your breadboard due to the self-inductance of the power distribution wires if this capacitor is not installed. Such voltage drops can make your circuit randomly malfunction, and sometimes even break into undesired oscillation. Here is a helpful analogy: Have you ever been in the shower when your roommate flushed the toilet? Ouch! The sudden cold water (current) demand made by the toilet as it flushes causes a sudden pressure (voltage) drop in the cold water supply (dc power bus) pipe, which makes a neighboring device, in this case the shower, that is also connected to the water supply pipe malfunction, resulting in your getting scalded! This is due to the inertia of the water (inductance of the dc power bus wires) and the narrowness and length of the water supply pipe (resistance of the dc power bus wires). The solution? Add a “local reservoir of charge”, that is, a small water tank (an ac bypass capacitor) near the toilet to locally supply the sudden water demand made by the toilet as it flushes. Now the water pressure in the pipe will not momentarily fall as the toilet is flushed, allowing the shower to continue working properly. Of course, it is important that the toilet not be flushed again until the small reservoir (capacitor) has time to recharge at a slow rate that does not cause a large pressure drop on the water pipe.
- c. Always cut your resistor and capacitor component leads short in order to minimize the amount of bare wire that is exposed on the board. Then interconnect your components with reasonably short lengths of insulated hookup wire. Note how this rule has been followed in Fig. L6-2. Please note that this figure is NOT the exact circuit you are wiring, but it is a very similar one!

- d. *Never* wire a lot of components directly to the terminals of the transistor, as this will result in a cluttered area that may lead to an undesired short-circuit. Also, keeping your transistor clear of many other components makes it easier to change out the BJT, or to probe the terminals of the BJT during circuit debugging. Instead, run a single wire from each transistor terminal over to a less crowded area of the breadboard, where the components can be located. See, for example, how the base bias resistors (R1 and R2) and the input coupling capacitor (CB) have been moved off to the left of the BJT in Fig. L6-2. Note how the collector pull-up resistor and the output coupling capacitor and the load resistor (RC and CC and RL) have been moved off to the right of the BJT. Similarly, note how the emitter resistor and the emitter bypass capacitor (RE and CE) have been placed well away from the BJT on the breadboard.
- e. *Never* try to bend the BJT leads into a different order, but rather keep them in the same order that they come out of the BJT case. If you try bending the leads into a new order, you will likely short out two of the three BJT terminals, which could possibly burn out the BJT!
- f. *Always* observe the polarities of electrolytic capacitors (CB, CC, and CE). The (+) terminal must connect to the node that is at the higher average dc potential, in order for the electrolytic capacitor to maintain its dielectric so that it will function properly.

**Figure L6-2 Photograph of a SIMILAR (But not identical) CE Amplifier Circuit  
(Keep your wires short, component leads cut short, etc.)**



- 3) With the function generator **OFF**, use your bench DVM to measure the dc Q-point. Do this by directly measuring  $V_{CEQ}$  and  $V_{BEQ}$ . Then indirectly measure  $I_{CQ}$  by measuring the voltage across  $R_C$ , and then divide this voltage by  $R_C$  to obtain  $I_{CQ}$ . How close did your measured Q-point come to the desired design goals that you started with in Part 2? (**NOTE: Because your resistor values will be only + or - 10% of the calculated values, and because you are using the simplest possible BJT model, if you are within plus or minus 20% of the design value, you are fine!**)

Measured Results:  $V_{BEQ} =$  \_\_\_\_\_  $V_{CEQ} =$  \_\_\_\_\_  $I_{CQ} =$  \_\_\_\_\_



Design Goals	0.7 V	11.0 V	15 mA
Percent Deviation:	_____	_____	_____

**Note: WHEN TROUBLESHOOTING ANY BJT AMPLIFIER, YOU SHOULD ALWAYS CHECK THE DC OPERATING Q-POINT FIRST BEFORE BOTHERING TO CHECK ITS AC PERFORMANCE, SINCE IF THE Q-POINT IS WAY OFF, THERE IS NO WAY THAT THE AC PERFORMANCE WILL BE CORRECT!**

- 4) Now you must set up your Agilent function generator to “**Hi-Z**” output mode, as was done in the previous lab project. Now set your function generator so that it delivers a **10 mV peak-to-peak, 1 kHz** sine wave when the function generator is connected across the input terminals of the amplifier. Next, connect the function generator to the input terminals of your amplifier circuit (making sure that dc power has been applied to your circuit), and place an oscilloscope probe across the generator terminals in order to monitor the input voltage,  $v_i(t)$ , delivered to the input terminals of the amplifier. You will find that “**autoscale**” does not work with such low signal levels, so you will have to manually adjust the channel sensitivity and sweep rate knobs in order to display the signal. You will probably find that the 10 mV peak-peak sine wave input signal displayed on the oscilloscope is quite “fuzzy”. This is because there is a large amount of high-frequency radio interference present on the Rose-Hulman campus, probably due to nearby computers. In order to remove this high frequency noise, we may average several (say 64) samples of the  $v_i(t)$  waveform. This averaging process will preserve the periodic signal, which adds *coherently* from one sample to the next, assuming that the signal has been properly triggered, so that the displayed periodic waveform is stationary. The high frequency noise, on the other hand, will add *incoherently*, and thus will be largely cancelled out in the averaging process.

To use the signal averaging feature of the Agilent 54622D digital oscilloscope, first make sure that the unaveraged  $v_i(t)$  waveform is properly triggered (stationary). You may have to adjust the “trigger level” knob on the right-hand side of the oscilloscope panel. Then hit the “**Acquire**” button, and then press the “**Averaging**” soft key located under the scope display. Next, hit the “**# Avgs**” soft key, and select “**64**” with the selector knob located to the right of the scope display. Now the  $v_i(t)$  waveform should now look much less fuzzy!

Once the oscilloscope is in averaging mode, the “**Quick Measure**” feature of the oscilloscope can be used to read the peak-to-peak value of  $v_i(t)$  reliably. You will find that the peak-to-peak value of  $v_i(t)$  displayed on the oscilloscope is a little bit less than the peak-to-peak voltage displayed on the function generator. This is due to the fact that the function generator is “loaded” by the input resistance of the amplifier due to the internal  $R_s = 50$  ohm resistance of the function generator, as shown inside the dotted box in Fig. L6-1. Some of the available function generator voltage (as displayed on the function generator) is lost across the internal resistance of the meter. Make a slight upward adjustment in the function generator output voltage amplitude, so that the peak-peak value of  $v_i(t)$  as read on the scope corresponds to 10 mV peak-peak. By simultaneously displaying the peak-to-peak voltage both at the input terminals,  $v_i(t)$ , and at the output terminals,  $v_o(t)$ , you can take the ratio of these two readings to measure the voltage gain,  $A_{vt} = v_o(t) / v_i(t)$  of this amplifier. (Hint: your observed value of  $A_{vt}$  should be close to the value predicted in the prelab. If your observations deviate by more than + or – 25% from this value, see the instructor.)

Remember to hit the “*Normal*” soft key to exit the averaging mode when you are ready to go on to the next measurement. If you forget and keep the scope in averaging mode as you probe a new point in your circuit, your scope display will often be incorrect, since the new waveform may not be properly triggered. While in averaging mode, if the averaged periodic signal (which should be largely noise-free) begins to undulate slowly in amplitude, this is a sign that your signal has lost triggering. If this happens, you must exit the averaging mode by hitting the “*Normal*” soft key, and take steps to re-trigger the signal to make it stationary before re-entering the averaging mode.

Include a copy of the oscilloscope screen showing both  $v_{in}(t)$  and  $v_o(t)$  as **Exhibit D**. Make sure the scope capture shows the peak to peak magnitude of both waves and then calculate the observed transducer voltage gain,  $A_{vt} = v_o(t) / v_{in}(t)$  directly below the waveform as part of the attachment.

Does  $v_o(t)$  appear to be a perfectly undistorted (though inverted) sinusoid? Recall that our in-class amplifier analysis has assumed “small signal” deviations about a bias point. However, in this case,  $v_o(t)$  should have an amplitude of about  $A_{vo} * 10$  mV peak-peak, which may be on the order of 1 volt peak-peak. This is *not* such a small deviation from the Q-point. Some small degree of distortion might be expected. Compare your observed value of  $A_{vt}$  with the value of  $A_{vt}$  *predicted by your hand calculations* (calculate % error).

Repeat your gain measurements with the emitter bypassed capacitor  $C_E$  removed. For this case, you may increase the signal strength to 100 mV peak-peak, since the gain of the amplifier is much lower now. (Hint: your  $A_{vt}$  value should be close to the value predicted in the prelab. If it is far from this value, see the instructor.) Include a scope capture of  $v_{in}(t)$  and  $v_o(t)$  with the emitter bypass capacitor removed as **Exhibit E**. Again make sure to show the peak to peak amplitudes of both waves and to calculate the gain based on the measured amplitudes directly on the attachment.

	CE Present		CE Removed
Observed $A_{vt} =$	_____	Observed $A_{vt} =$	_____
Predicted $A_{vt} =$	_____	Predicted $A_{vt} =$	_____
Percent Deviation =	_____	Percent Deviation =	_____

- 5) Now (with  $C_E$  placed back in the circuit) gradually increase the amplitude of your input *sinusoidal* source upward from 10 mV peak-peak. At some point, either the positive or the negative peak of the sinusoidal output waveform  $v_o(t)$  should begin to distort (flatten). Increase the input level until both the positive and negative peaks of the waveform are *clearly flattened*. Include a scope capture of  $v_{in}(t)$  and the distorted  $v_o(t)$  as **Exhibit F1**. On this screen capture, display maximum and minimum  $v_o(t)$  voltage excursions. The difference between  $V_{max}$  and  $V_{min}$  shall be called “*maximum asymmetrical output voltage swing*”.

Then decrease the input amplitude until the point is reached where the output waveform has *only one* of its peaks beginning to clearly flatten. Include a scope capture of  $v_{in}(t)$  and the (still somewhat) distorted  $v_o(t)$  as **Exhibit F2**. On this screen capture, display maximum and minimum  $v_o(t)$  voltage excursions. The difference between  $V_{max}$  and  $V_{min}$  shall be called “*maximum symmetrical output voltage swing*”

- 6) Sketch both the DC and the AC load lines for this circuit *directly over* the BJT’s common-emitter “ $I_c$  vs.  $V_{ce}$ ” characteristics that you plotted in Part 1. Next, use the AC load line, as explained in the section below (***Review of Maximum Symmetrical Voltage Swing Calculation***) to

approximately predict the maximum asymmetrical and symmetrical  $v_o(t)$  waveform swing. Note that positive  $v_o(t)$  peak flattening corresponds to driving the BJT into cutoff, while negative peak flattening corresponds to driving the BJT into saturation. Note that the  $v_o(t)$  waveform is the  $v_{ce}(t)$  waveform with its dc component removed by the output coupling capacitor.

Show your calculations in the space below, and fill in the blanks below that compare the observed maximum asymmetrical and symmetrical  $v_o(t)$  swing with your predictions. Your predicted and observed distortion points should agree within + or - 20%.

***Calculation of maximum asymmetrical and symmetrical  $v_o(t)$  output voltage swing***

**Predicted and observed distorted maximum asymmetrical  $v_o(t)$  swing**

$V_{o(t)}$  max asymm swing (predicted) = \_\_\_\_\_ V peak-to-peak

$V_{c(t)}$  max asymm swing (observed) = \_\_\_\_\_ V peak-to-peak

% deviation = \_\_\_\_\_

**Predicted and observed distorted maximum symmetrical  $v_o(t)$  swing**

$V_{o(t)}$  max symm swing (predicted) = \_\_\_\_\_ V peak-to-peak

$V_{c(t)}$  max symm swing (observed) = \_\_\_\_\_ V peak-to-peak

% deviation = \_\_\_\_\_



### ***Review of Maximum Symmetrical Vce(t) Swing Calculation***

The “dc” bias load line is determined by writing KVL around the collector loop in the dc model of the circuit shown in Fig. L6-1. Assuming  $I_c$  is approximately equal to  $I_e$  yields:

$$V_{cc} = I_c R_c + V_{ce} + I_c R_e + V_{ee} \quad \Rightarrow \quad I_c = -V_{ce}/(R_c + R_e) + (V_{cc} - V_{ee})/(R_c + R_e)$$

Note that  $V_{cc} = +12$  V and  $V_{ee} = -12$  V. Thus the dc load line has an  $I_c$  axis intercept of  $(V_{cc} - V_{ee})/(R_c + R_e)$  and a  $V_{ce}$  axis intercept of  $(V_{cc} - V_{ee}) = 24$  V; it has a slope of  $-1/(R_c + R_e)$ ; and it must intersect the BJT’s  $I_c$  vs.  $V_{ce}$  curve corresponding to  $I_b = I_{bQ}$  at the quiescent operating (Q) point.

The dynamic “ac” load line still passes through the Q-point, but it has a steeper slope than the dc load line. This is because in the ac model of the circuit of Fig. L6-1, the emitter resistor is short-circuited, and  $R_c$  is effectively connected in parallel with  $R_L$ . The slope of the dynamic (ac) load line is determined by applying KVL around the output loop in the ac model of the common emitter BJT amplifier, which reveals

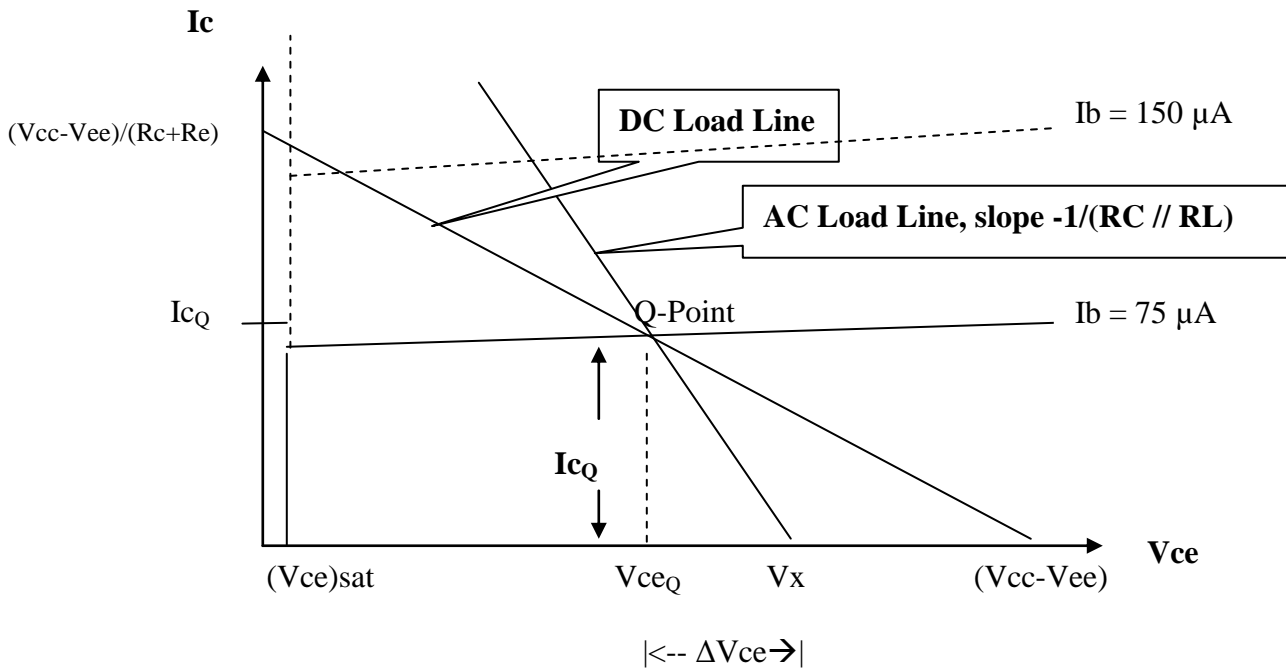
$$v_{CE}(t) = - (R_c // R_L) i_c(t)$$

Solving for  $i_c(t)$ :

$$i_c(t) = -v_{CE}(t)/(R_c // R_L)$$

Thus the slope of the ac load line will be *steeper* than the slope of the dc load line, since the dc load line has a slope of  $-1/(R_c + R_e)$ , and the ac load line has a slope of  $-1/(R_c // R_L)$ . Note that when the complete  $I_c(t)$  and  $V_{ce}(t)$  waveforms are considered (where the ac and dc parts of this problem are superimposed), this ac load line must still pass through the dc Q-point. The dc and ac load lines are plotted over the collector characteristics for a BJT in Fig. L6-3. Note that with the much steeper slope, even relatively small ac output voltage variations (resulting in excursions from  $V_{CEQ}$  of just a few volts) can cause the BJT to enter cutoff, thus resulting in a clipping-type of distortion as the sinusoidal source amplitude is increased, causing the amplitude of  $v_o(t) = v_{CE}(t)$  to rise to the point where the BJT enters cutoff on the high end, and saturation on the low end of the AC load line.

**Fig. L6-3 Example BJT Collector Characteristic with dc and ac lines for CE amplifier**



Thus to find the maximum symmetrical swing, we know the slope of the AC load line may be calculated two different ways:

$$\text{Slope AC Load Line} = -1/(R_c // R_L) = -I_{cQ} / \Delta V_{ce}$$

We may solve for  $\Delta V_{ce}$ , which is the amount that  $V_{ce}$  may rise above the Q-point value ( $V_{ceQ}$ ) before the BJT leaves the active (amplifying) region and enters cutoff. Also, we must calculate the amount  $V_{ce}$  may fall below  $V_{ceQ}$  before it leaves the active region and enters saturation, which is given by  $(V_{ceQ} - (V_{ce})_{sat})$ . Since we usually want to know the maximum symmetrical swing of the output voltage  $V_{ce}(t)$  about the Q-point, we take the smaller of these two calculated voltage swings as setting the maximum symmetrical swing.

For the drawing above, it is clear that  $(V_x - V_{ceQ}) < (V_{ceQ} - (V_{ce})_{sat})$ , so the maximum symmetrical swing is given by

$$\underline{\text{Max Symmetrical Output Voltage Swing}} = 2(V_x - V_{ceQ}) = 2\Delta V_{ce} \quad (\text{Volts, peak-to-peak})$$

The highest possible value of  $V_{ce}$  is:

$$(V_{ce})_{max} = V_x = V_{ceQ} + \Delta V_{ce}$$

The lowest possible value of  $V_{ce}$  is:

$$(V_{ce})_{min} = (V_{ce})_{sat}.$$

$$\begin{aligned} \Rightarrow \underline{\text{Max Asymmetrical Output Voltage Swing}} &= (V_{ce})_{max} - (V_{ce})_{min} \\ &= V_x - (V_{ce})_{sat} \quad (\text{Volts, peak-to-peak}) \end{aligned}$$

## **Appendix A. ECE250 Using the Sony-Tektronix 370 Curve Tracer To Trace Common-Emitter $I_c$ vs. $V_{ce}$ curves of an NPN BJT**

1. Depress **POWER** on/off button to turn on the power to the curve tracer, if necessary. (This button is located at the extreme lower right of the panel).
2. Depress the “**STANDBY**” device selector button located at the lower left of the panel. This disconnects both devices from the curve tracer until it is properly set up.
3. Gently tilt up the plastic electrical safety interlock protection shield, and insert a BJT in the lower right and/or in the lower left BJT socket. For the 2N2222A, with the flat side facing toward you, the pins come out the bottom in C B E order.
4. Close the plastic shield, as the curve tracer will NOT operate unless this safety interlock shield is closed, as a safety precaution.
5. Adjust the “**VERTICAL Current/Div**” selector knob (upper middle of panel) to “**5 mA/div**”. This value is displayed at the upper right of the oscilloscope display (See Fig. 3-26). If this value is not visible, try advancing the “**Readout/Cursor Intensity**” knob located to the right of the oscilloscope display. (Once the curve has been displayed, this setting may be adjusted as desired.)
6. Adjust the “**HORIZONTAL Volts/Div**” selector knob if the number to **2V/div**. . (Once the curve has been displayed, this setting may be adjusted as desired.)
7. Turn the “**STEP/OFFSET Amplitude**” selector knob clockwise to **50  $\mu$ A**. This makes the current step generator (See Figure 3-25) generate base current ( $I_b$ ) current steps with a current increment between adjacent steps of  $\Delta I_b = 50 \mu A$ . (The “+” current polarity should be selected for an NPN BJT, if not depress the **INVERT** button to select it.) . (Once the curve has been displayed, this setting may be adjusted as desired.)
8. Set the “**Collector Supply Max Peak Power Watts**” selector paddle switch to **0.4 W** (this paddle is located on the lower right panel). (This permits more of the curves to be displayed in the high current, high voltage region of the  $I_c$  vs.  $V_{ce}$  plot.)
9. Finally, hit the “**LEFT**” or the “**RIGHT**” device select button (located at the lower left of the panel) to display the “ $I_c$  vs.  $V_{ce}$ ” family of curves (one curve for  $I_b = 0$ , one for  $I_b = 50 \mu A$ , one for  $I_b = 100 \mu A$ , one for  $I_b = 150 \mu A$ , etc.) for either the BJT in the left or the right socket, as selected.
10. At this point, a white dot should appear at the lower left of the oscilloscope display screen. If not, try turning up the top-most intensity knob located to the right of the oscilloscope display. Advance the large “**VARIABLE**” knob located at the far lower right of the panel, in order to display the family of common-emitter BJT curves, as depicted in Fig. 3-26.
11. You may want to make further adjustments in the **VERTICAL Current/Div** knob, the **HORIZONTAL Volts/Div** knob, the **STEP/OFFSET Amplitude** knob, and the “**NUMBER OF STEPS**” selector paddle to suit your taste.
12. Note that  $\beta$  can now be read as  $\Delta I_c / \Delta I_b$  from the oscilloscope display of the family of  $I_c$  vs.  $V_{ce}$  curves, where  $\Delta I_c$  is the vertical distance between adjacent curves in the vicinity of the desired Q-point, and  $\Delta I_b$  is the current increment step that was chosen back in Step 7 (in our example,  $\Delta I_b = 50 \mu A$ ). Note that  $\beta$  can be read even more conveniently by using the “ **$\beta$ /div = 100**” number that is automatically displayed for us by the curve tracer, as seen in Fig. 3-26. The curve tracer saves us the inconvenience of having to do any calculation by making the following calculation for us:

$$\beta/\text{div} = \Delta I_c / \Delta I_b = (5 \text{ mA/div}) / 50 \mu A = 100.$$

13. You can compare two BJTs easily by alternately depressing the “**LEFT**” and “**RIGHT**” device selector buttons. This permits two BJTs to be selected that have nearly the same characteristics, as is sometimes required in a circuit.

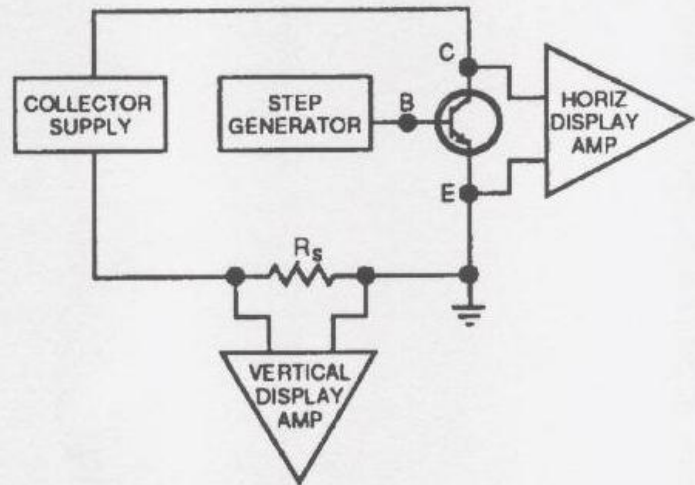
**Appendix B.****Basic Operation of Curve Tracer --- From Tektronix Curve Tracer Manual)**

Figure 3-25: Bipolar Transistor Common-emitter Config

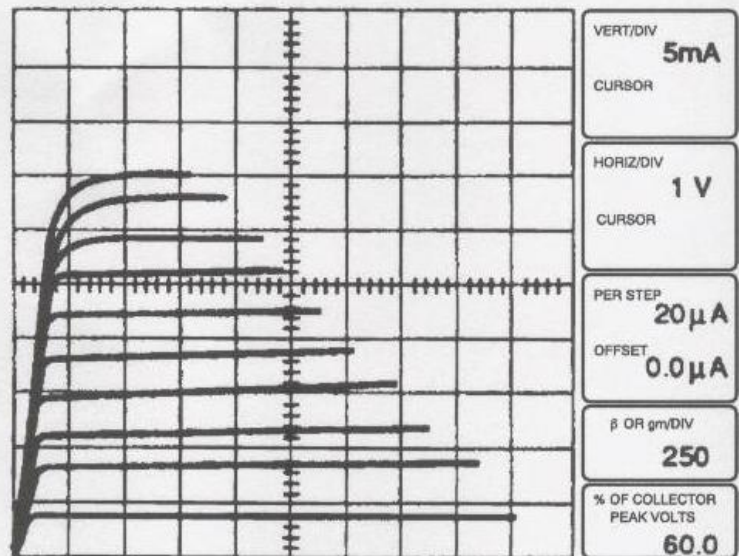


Figure 3-26: Bipolar Transistor Family of Curves